

END SUMMARY  
FOR PAPER NO. 5

L Number	Hits	Search Text	DB	Time stamp
1	19	"5661056"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/08 17:16
-	19	"5619052"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/08 15:59
-	22	"4808259"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/08 16:00
-	2	jp-63058959-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/08 17:16

CLIPPEDIMAGE= JP363058959A

PAT-NO: JP363058959A

DOCUMENT-IDENTIFIER: JP 63058959 A

TITLE: FIELD-EFFECT TYPE SEMICONDUCTOR DEVICE WITH  
CAPACITOR

PUBN-DATE: March 14, 1988

INVENTOR-INFORMATION:

NAME

SADAHIRO, SHIGEKI

ASSIGNEE-INFORMATION:

NAME

MITSUBISHI ELECTRIC CORP

COUNTRY

N/A

APPL-NO: JP61204504

APPL-DATE: August 29, 1986

INT-CL (IPC): H01L027/10;H01L027/04 ;H01L029/78

US-CL-CURRENT: 257/310

ABSTRACT:

PURPOSE: To secure the capacitor capacity which is necessary and sufficient for a memory action and to keep the high reliability of the action by using silicon oxynitride for a capacitor gate insulating film.

CONSTITUTION: A silicon oxynitride film 5 as a capacitor gate insulating film is formed by means of an LPCVD method. The silicon oxynitride film 5 has a property which is intermediate between an oxide film and a nitride film, and its dielectric constant, leakage current, etc., can be arbitrarily changed within the range of the attribute of two types of films if the ratio of the flow rate of a reaction gas is set appropriately. Because

the excellent  
thin-filmed characteristic is realized by making use of the  
LPCVD method, it is  
possible to satisfy the required specifications for an  
individual semiconductor  
device and to realize an optimum condition to form the  
capacitor gate  
insulating film so that the reliability can be improved.

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DERWENT-ACC-NO: 1988-109377  
DERWENT-WEEK: 198816  
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TITLE: FET type semiconductor device capacitor - has  
control insulation film,  
capacitor insulation film, capacitor control electrode and  
inter layer  
insulation film NoAbstract Dwg 1/2

PATENT-ASSIGNEE: MITSUBISHI DENKI KK[MITQ]

PRIORITY-DATA: 1986JP-0204504 (August 29, 1986)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE
PAGES	MAIN-IPC	
JP 63058959 A	March 14, 1988	N/A
012	N/A	

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO
APPL-DATE		
JP63058959A	N/A	1986JP-0204504
August 29, 1986		

INT-CL (IPC): H01L027/10; H01L029/78

ABSTRACTED-PUB-NO:

EQUIVALENT-ABSTRACTS:

TITLE-TERMS:

FET TYPE SEMICONDUCTOR DEVICE CAPACITOR CONTROL INSULATE  
FILM CAPACITOR  
INSULATE FILM CAPACITOR CONTROL ELECTRODE INTER LAYER  
INSULATE FILM NOABSTRACT

DERWENT-CLASS: U12

EPI-CODES: U12-C02A; U12-C02A1; U12-D02A;